

ABSTRACT OF THE DISCLOSURE

In a semiconductor device having a substrate which has a metal surface, an insulating film which is formed on the substrate having the metal surface, and a pixel unit which is formed on the insulating film; the pixel unit includes a TFT, and wiring lines connected with the TFT, and a storage capacitor is constituted by the substrate (11) having the metal surface, the insulating film (12), and the wiring line (21). As the insulating film is thinner, and as the area of a region where the insulating film and the wiring line lie in contact is larger, the storage capacitor is endowed with a larger capacity.